

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in this application:

1-41 (Canceled).

42. (Previously Presented) A camera having at least one reflection type liquid crystal device, said reflection type liquid crystal device comprising:

a thin film transistor being formed over a first substrate;
an interlayer insulating film being formed over the thin film transistor and the first substrate;
a pixel electrode comprising a metal and being formed over the interlayer insulating film; and
a reflection layer comprising a dielectric multi-layer film and being formed on the pixel electrode;

wherein convex or concave portions are formed on the interlayer insulating film, so that a surface of the pixel electrode has convex or concave portions;

wherein the dielectric multi-layer film comprises a first thin film having a first refractive index and a second thin film having a second refractive index formed on the first thin film;

wherein the second refractive index is higher than the first refractive index;

wherein the second refractive index is in a range of 1.8 to 6.0; and

wherein the first refractive index has a ratio of 0.7 or less with respect to the second refractive index.

43. (Currently Amended) A camera device according to claim 42,

wherein a film thickness d_1 of said first thin film is so adjusted as to satisfy $400 \text{ nm} \leq \underline{n_1} \leq 500 \text{ nm}$ ($\underline{n_1} = 4n_1d_1$), where the film thickness and the refractive index of said first thin film are d_1 and n_1 , respectively; and

wherein a film thickness d_2 of said second thin film is so adjusted as to satisfy $450 \text{ nm} \leq \underline{n_2} \leq 700 \text{ nm}$ ($\underline{n_2} = 4n_2d_2$), where the film thickness and the refractive index of said second thin film are d_2 and n_2 , respectively.

44-46. (Cancelled)

47. (Previously Presented) A camera according to claim 42, wherein the pixel electrode comprises a material selected from the group consisting of aluminum and silver.

48. (Previously Presented) A camera according to claim 42, wherein the pixel electrode is formed on the interlayer insulating film in contact therewith.

49. (Previously Presented) A camera according to claim 42, wherein the reflection type liquid crystal device comprising: a second substrate being opposed to the first substrate; a liquid crystal material being sealed between the first and second substrates; the pixel electrode being arranged in a matrix manner over the first substrates; a thin film transistor being connected to the pixel electrode; and the reflection layer.

50. (Previously Presented) A camera according to claim 42, wherein the camera is a digital

camera.

51. (Previously Presented) A camera according to claim 42, wherein the camera is a digital still camera.

52. (Previously Presented) A personal computer having at least one reflection type liquid crystal device, said reflection type liquid crystal device comprising:

a thin film transistor being formed over a first substrate; an interlayer insulating film being formed over the thin film transistor and the first substrate;

a pixel electrode comprising a metal and being formed over the interlayer insulating film;

a reflection layer comprising a dielectric multi-layer film and being formed on the pixel electrode;

wherein convex or concave portions are formed on the interlayer insulating film, so that a surface of the pixel electrode has convex or concave portions;

wherein the dielectric multi-layer film comprises a first thin film having a first refractive index and a second thin film having a second refractive index formed on the first thin film;

wherein the second refractive index is higher than the first refractive index; and

wherein the second refractive index is in a range of 1.8 to 6.0, and

wherein the first refractive index has a ratio of 0.7 or less with respect to the second refractive index.

53. (Currently Amended) A personal computer according to claim 52,

wherein a film thickness d_1 of said first thin film is so adjusted as to satisfy $400 \text{ nm} \leq d_1 \leq 500 \text{ nm}$ ($d_1 = 4n_1d_1$), where the film thickness and the refractive index of said first thin film are d_1 and n_1 , respectively, and a film thickness d_2 of said second thin film is so adjusted as to satisfy $450 \text{ nm} \leq d_2 \leq 700 \text{ nm}$ ($d_2 = 4n_2d_2$), where the film thickness and the refractive index of said second thin film are d_2 and n_2 , respectively.

54-56. (Cancelled)

57. (Previously Presented) A personal computer according to claim 52, wherein the pixel electrode comprises a material selected from the group consisting of aluminum and silver.

58. (Previously Presented) A personal computer according to claim 52, wherein the pixel electrode is formed on the interlayer insulating film in contact therewith.

59. (Previously Presented) A personal computer according to claim 52, wherein the reflection type liquid crystal device comprising: a second substrate being opposed to the first substrate; a liquid crystal material being sealed between the first and second substrates; the pixel electrode being arranged in a matrix manner over the first substrates; a thin film transistor being connected to the pixel electrode; and the reflection layer.

60. (New) A cellular phone having at least one reflection type liquid crystal device, said reflection type liquid crystal device comprising:

a thin film transistor being formed over a first substrate;
an interlayer insulating film being formed over the thin film transistor and the first substrate;
a pixel electrode comprising a metal and being formed over the interlayer insulating film; and
a reflection layer comprising a dielectric multi-layer film and being formed on the pixel electrode;

wherein convex or concave portions are formed on the interlayer insulating film, so that a surface of the pixel electrode has convex or concave portions;

wherein the dielectric multi-layer film comprises a first thin film having a first refractive index and a second thin film having a second refractive index formed on the first thin film;

wherein the second refractive index is higher than the first refractive index;

wherein the second refractive index is in a range of 1.8 to 6.0; and

wherein the first refractive index has a ratio of 0.7 or less with respect to the second refractive index.

61. (New) A cellular phone device according to claim 60,

wherein a film thickness d_1 of said first thin film is so adjusted as to satisfy $400 \text{ nm} \leq .1 \leq 500 \text{ nm}$ ($.1 = 4n_1d_1$), where the film thickness and the refractive index of said first thin film are d_1 and n_1 , respectively; and

wherein a film thickness d_2 of said second thin film is so adjusted as to satisfy $450 \text{ nm} \leq .2 \leq 700 \text{ nm}$ ($.2 = 4n_2d_2$), where the film thickness and the refractive index of said second thin film are d_2 and n_2 , respectively.

62. (New) A cellular phone according to claim 60, wherein the pixel electrode comprises a material selected from the group consisting of aluminum and silver.

63. (New) A cellular phone according to claim 60, wherein the pixel electrode is formed on an interlayer insulating film in contact therewith.

64. (New) A cellular phone according to claim 60, wherein the reflection type liquid crystal device comprising: a second substrate being opposed to the first substrate; a liquid crystal material being sealed between the first and second substrates; the pixel electrode being arranged in a matrix manner over the first substrate; the thin film transistor being connected to the pixel electrode; and the reflection layer.

65. (New) A cellular phone according to claim 60, wherein the pixel electrode comprises a material selected from the group consisting of aluminum and silver.

66. (New) A cellular phone according to claim 60, wherein the pixel electrode is formed on the interlayer insulating film in contact therewith.

67. (New) A cellular phone according to claim 60, wherein the reflection type liquid crystal device comprising: a second substrate being opposed to the first substrate; a liquid crystal material being sealed between the first and second substrates; the pixel electrode being arranged in a matrix manner over the first substrates; a thin film transistor being connected to the pixel electrode; and the

reflection layer.

68. (New) An electronic device having an active matrix display device comprising:

- a switching element formed over a first substrate;
- a first interlayer insulating film formed over the switching element;
- a second interlayer insulating film comprising an organic resin formed over the first interlayer insulating film, a surface of said second interlayer insulating film having a plurality of first protrusions;
- a pixel electrode formed over the plurality of first protrusions, a surface of said pixel electrode having a plurality of second protrusions;
- a first dielectric layer formed over the pixel electrode;
- a second dielectric layer formed on the first dielectric layer, wherein said second dielectric layer has a different refractive index from said first dielectric layer; and
- an orientation film formed on the second dielectric layer.

69. (New) An electronic device according to claim 68, wherein the first dielectric layer comprises a material selected from the group consisting of SiO_2 , MgF_2 , Na_3AlF_6 .

70. (New) An electronic device according to claim 68, wherein the first dielectric layer comprises a material from the group consisting of TiO_2 , ZrO_2 , Ta_2O_5 , ZnS , ZnSe , ZnTe , Si , Ge , Y_2O_3 and Al_2O_3 .

71. (New) A camera having an active matrix display device comprising:
- a switching element formed over a first substrate;
 - a first interlayer insulating film formed over the switching element;
 - a second interlayer insulating film comprising an organic resin formed over the first interlayer insulating film, a surface of said second interlayer insulating film having a plurality of first protrusions;
 - a pixel electrode formed over the plurality of first protrusions, a surface of said pixel electrode having a plurality of second protrusions;
 - a first dielectric layer formed over the pixel electrode;
 - a second dielectric layer formed on the first dielectric layer, wherein said second dielectric layer has a different refractive index from said first dielectric layer; and
 - an orientation film formed on the second dielectric layer.
72. (New) A camera according to claim 71, wherein the first dielectric layer comprises a material selected from the group consisting of SiO_2 , MgF_2 , Na_3AlF_6 .
73. (New) A camera according to claim 71, wherein the first dielectric layer comprises a material from the group consisting of TiO_2 , ZrO_2 , Ta_2O_5 , ZnS , ZnSe , ZnTe , Si , Ge , Y_2O_3 and Al_2O_3 .
74. (New) A camera according to claim 71, wherein the camera is a digital camera.
75. (New) A camera according to claim 71, wherein the camera is a digital still camera.

76. (New) A cellular phone having an active matrix display device comprising:

- a switching element formed over a first substrate;
- a first interlayer insulating film formed over the switching element;
- a second interlayer insulating film comprising an organic resin formed over the first interlayer insulating film, a surface of said second interlayer insulating film having a plurality of first protrusions;
- a pixel electrode formed over the plurality of first protrusions, a surface of said pixel electrode having a plurality of second protrusions;
- a first dielectric layer formed over the pixel electrode;
- a second dielectric layer formed on the first dielectric layer, wherein said second dielectric layer has a different refractive index from said first dielectric layer; and
- an orientation film formed on the second dielectric layer.

77. (New) A cellular phone according to claim 76, wherein the first dielectric layer comprises a material selected from the group consisting of SiO_2 , MgF_2 , Na_3AlF_6 .

78. (New) A cellular phone according to claim 76, wherein the first dielectric layer comprises a material from the group consisting of TiO_2 , ZrO_2 , Ta_2O_5 , ZnS , ZnSe , ZnTe , Si , Ge , Y_2O_3 and Al_2O_3 .